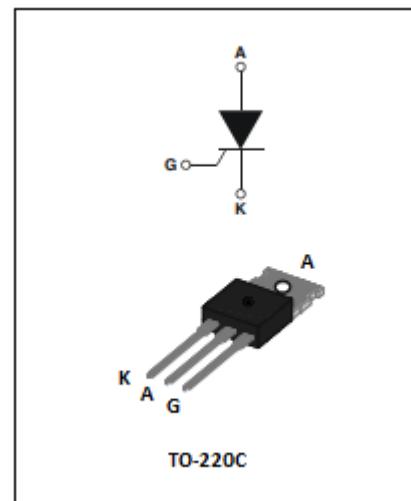


P/N: YZPST-S2535 Series 25A SCRs

Rev: 1.0

DESCRIPTION:

Glass passivated thyristors in a plastic envelope, The YZPST-S2535 SCRs series is suitable to fit all modes of control, found in applications such as overvoltage crowbar protection, motor control circuits in power tools and kitchen aids, inrush current limiting circuits, capacitive discharge ignition, Softstart AC motor control and voltage regulation circuits...



Symbol	Value	Unit
I _{T(RMS)}	40	A
V _{DRM} V _{RRM}	1200	V
I _{GT}	35	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T _{stg}	-40 ~ 150	°C
Operating junction temperature range	T _j	-40~125	°C
Repetitive peak off-state voltage (T =25°C)	V _{DRM}	1200	V
Repetitive peak reverse voltage (T =25°C)	V _{RRM}	1200	V
Non repetitive surge peak Off-state voltage	V _{DSM}	V _{DRM} +100	V
Non repetitive peak reverse voltage	V _{RSM}	V _{RRM} +100	V
RMS on-state current (T =100°C)	I _{T(RMS)}	40	A
Non repetitive surge peak on-state current	I _{TSM}	350	A
Average on-state current (180° conduction angle)	I _{T(AV)}	25	A
I ² t value for fusing (tp=10ms)	I ² t	450	A ² S
Critical rate of rise of on-state current (I =2×IGT, tr ≤ 100 ns)	dI/dt	150	A/μS
Peak gate current	I _{GM}	4	A
Average gate power dissipation	P _{G(AV)}	1	W

ELECTRICAL CHARACTERISTICS (T=25°C unless otherwise specified)

Symbol	Test Condition		Value	Unit
I _{GT}	V =12V R =140Ω	MAX.	35	mA
V _{GT}		MAX.	1.3	V
V _{GD}	V _D =V _{DRM} T _j =125°C R=1KΩ	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	MAX.	75	mA
I _H	IT=50mA	MAX.	50	mA
dV/dt	V _D =2/3V _{DRM} Gate Open T _j =125°C	MIN.	500	V/μs

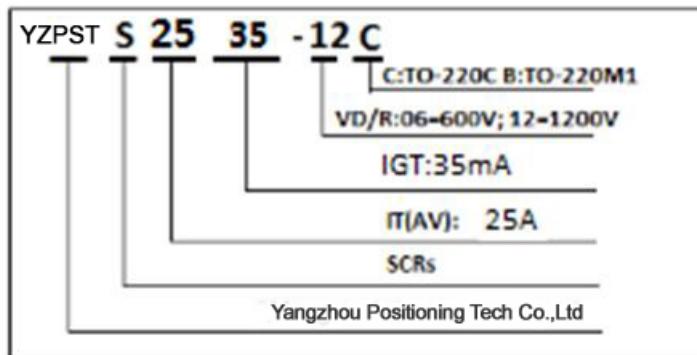
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =40A tp=380μs	T _j =25°C	1.65	V
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C	500	μA
I _{RRM}		T _j =125°C	6	mA

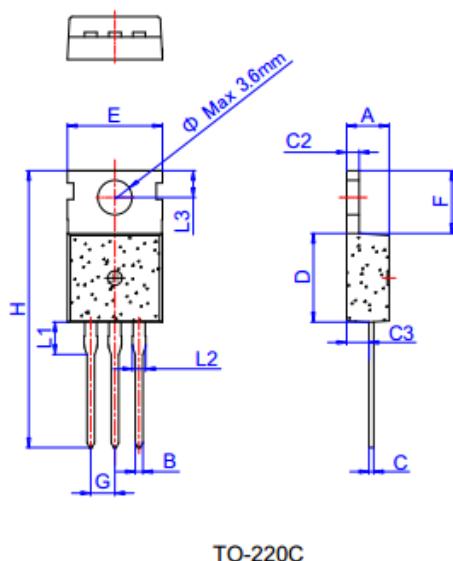
Thermal Resistances

Symbol	Parameter	Value(MAX.)	Unit
R _{th(j-a)}	junction to ambient(DC)	60	°C/W
R _{th(j-c)}	Junction to case (DC)	0.9	

Ordering information scheme



TO-220C Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	

FIG.1 power dissipation versus Average RMS on-state current

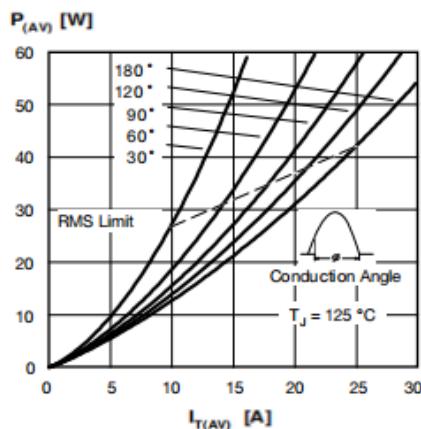


FIG.3: maximum Non repetitive Surge current

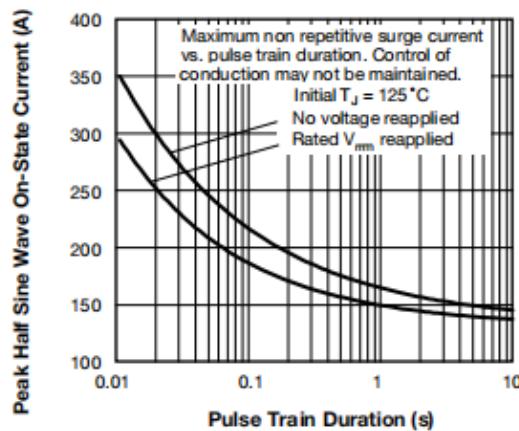


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<10ms, and corresponding value of $I^2 t$ ($dI/dt < 50A/\mu s$)

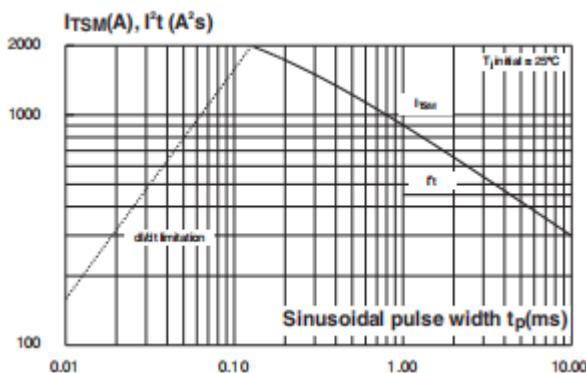


FIG.2: Average on-state current versus case temperature

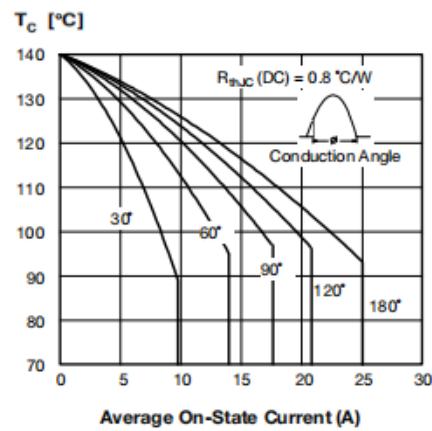


FIG.4: On-state characteristics (maximum values)

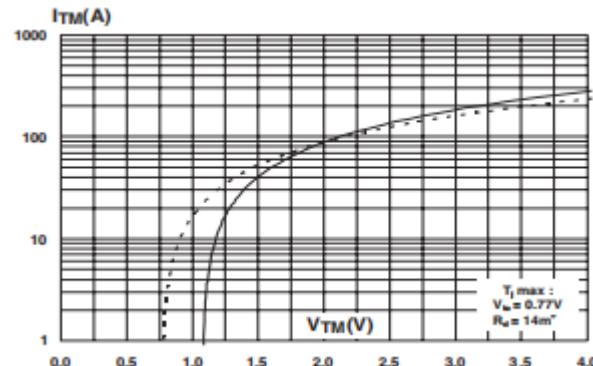


FIG.6: Relative variations of gate trigger current holding current and latching current versus junction temperature

